MOSFETs Silicon N-Channel MOS (DTMOSIV)

# TK10Q60W

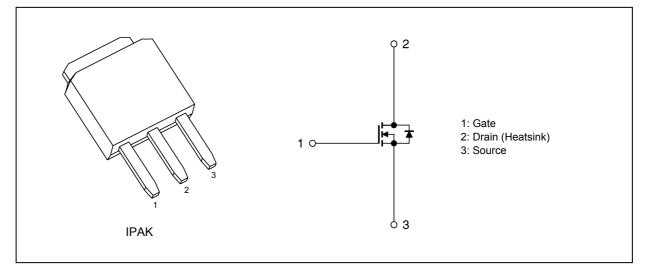
#### 1. Applications

Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.327 \Omega$  (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th}$  = 2.7 to 3.7 V (V\_{DS} = 10 V,  $I_{D}$  = 0.5 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics				Rating	Unit	
Drain-source voltage			V <sub>DSS</sub>	600	V	
Gate-source voltage			V <sub>GSS</sub>	±30	]	
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	9.7	A	
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	38.8	1	
Power dissipation	(T <sub>c</sub> = 25°C)		PD	80	W	
Single-pulse avalanche energy		(Note 2)	E <sub>AS</sub>	121	mJ	
Avalanche current			I <sub>AR</sub>	2.5	A	
Reverse drain current (DC)		(Note 1)	I <sub>DR</sub>	9.7	1	
Reverse drain current (pulsed)		(Note 1)	I <sub>DRP</sub>	38.8	1	
Channel temperature			T <sub>ch</sub>	150	°C	
Storage temperature			T <sub>stg</sub>	-55 to 150	1	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2012-09 2013-12-25 Rev.3.0

#### 5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	1.57	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	125	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V\_DD = 90 V, T\_ch = 25°C (initial), L = 33.9 mH, R\_G = 25  $\Omega$ , I\_AR = 2.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

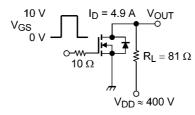
#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	600	_	—	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 mA	2.7	—	3.7	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.9 A		0.327	0.43	Ω

#### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	700	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	]	_	2.3	_	
Output capacitance	C <sub>oss</sub>	]	_	20	_	1
Effective output capacitance	C <sub>o(er)</sub>	$V_{DS} = 0$ to 400 V, $V_{GS} = 0$ V	—	35		
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz	_	7.5	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1	_	22	_	ns
Switching time (turn-on time)	t <sub>on</sub>	1	_	45	_	
Switching time (fall time)	t <sub>f</sub>	1		5.5	_	
Switching time (turn-off time)	t <sub>off</sub>	1	_	75	_	1
MOSFET dv/dt ruggedness	dv/dt	V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 4.9 A	50	_	_	V/ns



Duty  $\leq$  1%,  $t_W =$  10  $\mu s$ 

#### Fig. 6.2.1 Switching Time Test Circuit

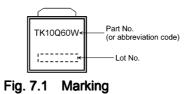
#### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V},  V_{GS} \text{ = } 10  \text{V},  \text{I}_{D} \text{ = } 9.7  \text{A}$	_	20	_	nC
Gate-source charge 1	Q <sub>gs1</sub>			4.5	_	
Gate-drain charge	Q <sub>gd</sub>		_	9.5	_	

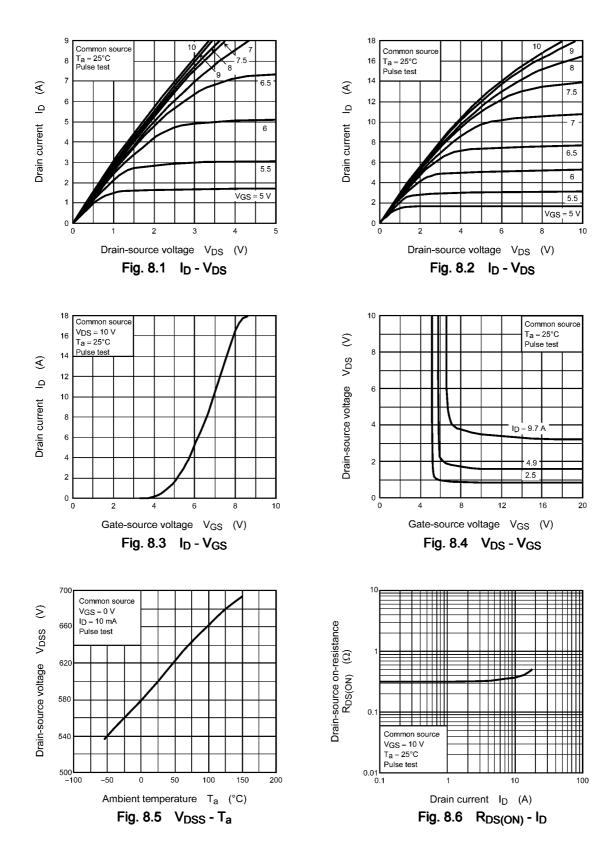
#### 6.4. Source-Drain Characteristics (Ta = 25°C unless otherwise specified)

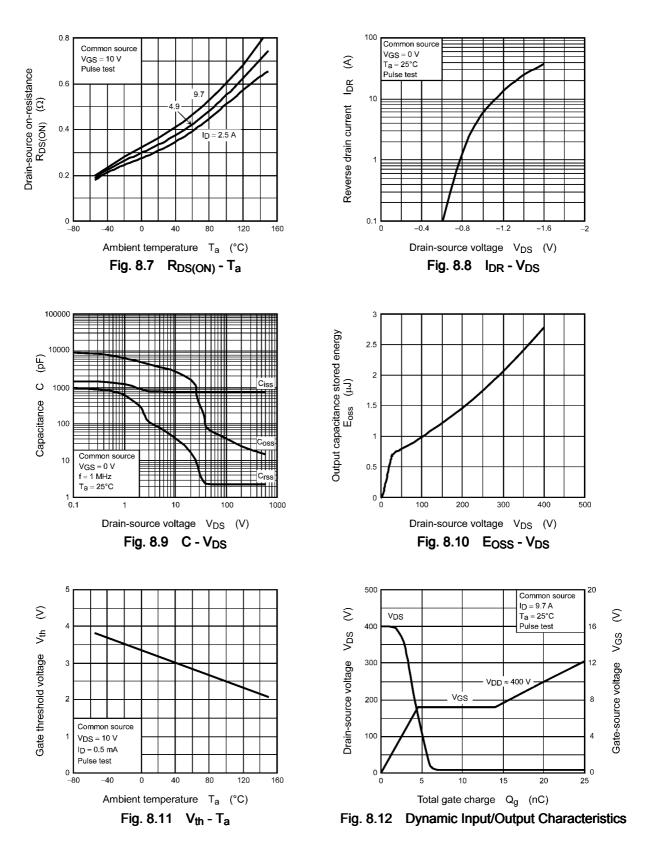
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 9.7 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 4.9 A, V <sub>GS</sub> = 0 V -dI <sub>DR</sub> /dt = 100 A/μs	_	250	_	ns
Reverse recovery charge	Q <sub>rr</sub>		_	2.2	_	μC
Peak reverse recovery current	I <sub>rr</sub>			19	_	А
Diode dv/dt ruggedness	dv/dt	$I_{DR}$ = 4.9 A, $V_{GS}$ = 0 V, $V_{DD}$ = 400 V	15			V/ns

### 7. Marking



#### 8. Characteristics Curves (Note)





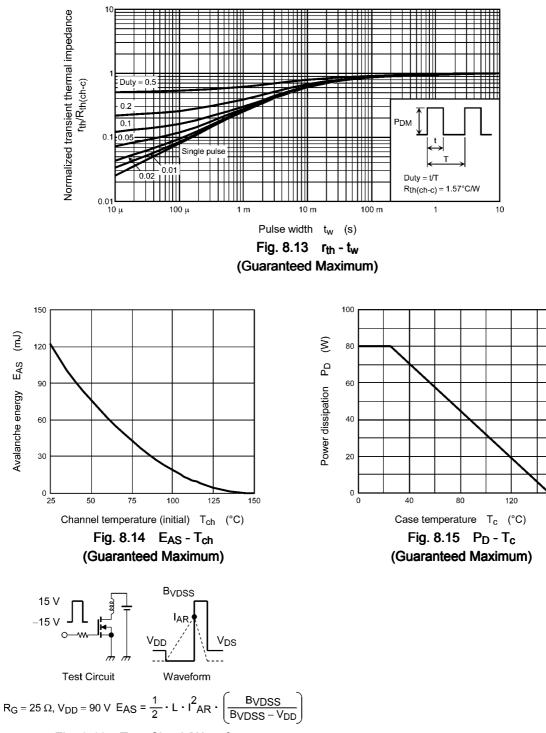
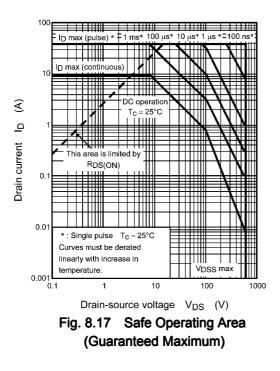


Fig. 8.16 Test Circuit/Waveform

160

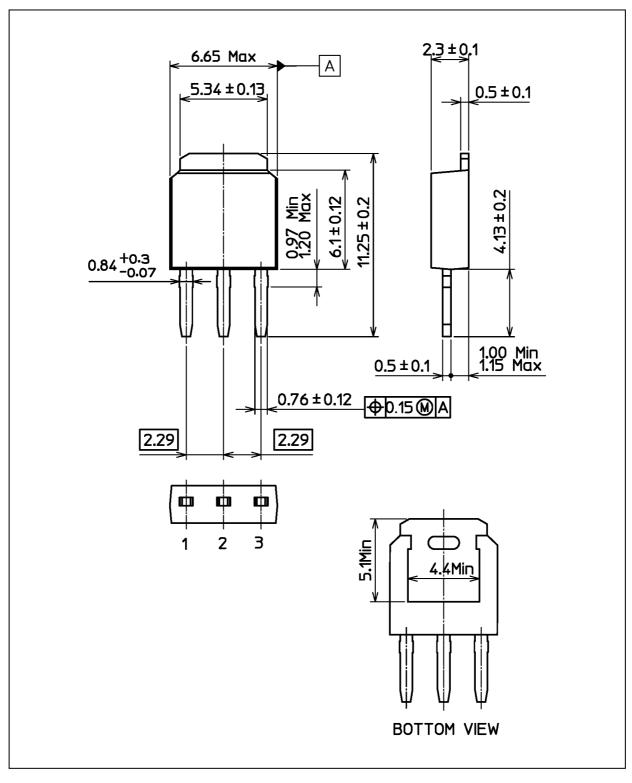


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



#### **Package Dimensions**

Unit: mm



Weight: 0.337 g (typ.)

Package Name(s)

TOSHIBA: 2-7L1A

Nickname: IPAK

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